

50V NPN MEDIUM POWER TRANSISTOR IN SOT23

Features

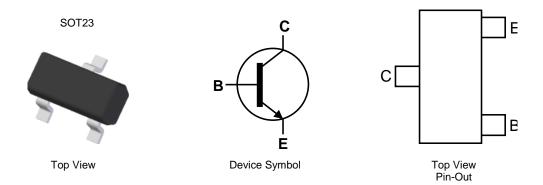
- BV_{CEO} > 50V
- BV_{CEV} > 80V Forward Blocking Voltage
- I_C = 5A high Continuous Collector Current
- I_{CM} = 12A Peak Collector Current
- Low Saturation Voltage, V_{CE(SAT)} < 40mV @1A
- $R_{CE(SAT)} = 24m\Omega$ for a Low Equivalent On-Resistance
- Complementary PNP Type: ZXTP2025F
- Totally Lead-Free & Fully RoHS compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

Mechanical Data

- Case: SOT23
- Case Material: Molded Plastic, "Green" Molding Compound UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Plated Leads, Solderable per MIL-STD-202, Method 208 (63)
- Weight 0.008 grams (Approximate)

Applications

- MOSFET and IGBT Gate Driving
- Motor Drive
- Relay Lamp and Solenoid Drive
- DC-DC Converters



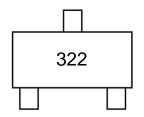
Ordering Information (Note 4)

Ī	Product	Compliance	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
	ZXTN2031FTA	AEC-Q101	322	7	8	3,000

Notes: 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.

- 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http"//www.diodes.com/products/packages.html.

Marking Information



322 = Product Type Marking Code

ZXTN2031F 1 of 7 October 2014

Document number: DS33666 Rev. 3 - 2 Downloaded From Oneyac.com Oneyac.com





Absolute Maximum Ratings (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V _{CBO}	80	V
Collector-Emitter Voltage	V _{CEV}	80	V
Collector-Emitter Voltage	V _{CEO}	50	V
Emitter-Base Voltage	V _{EBO}	7	V
Continuous Collector Current	Ic	5	Α
Peak Pulse Current	I _{CM}	12	Α
Base Current	I _B	1.2	Α

Thermal Characteristics (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit		
	(Note 5)		1.0 8.0		
Power Dissipation Linear Derating Factor	(Note 6)	P_{D}	1.2 9.6	W mW/°C	
	(Note 7)		1.56 12.5		
	(Note 5)		125		
Thermal Resistance, Junction to Ambient	(Note 6)	$R_{\theta JA}$	104	°C/W	
	(Note 7)		80		
Thermal Resistance, Junction to Lead	(Note 8)	R _{0JL}	57	°C/W	
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C		

ESD Ratings (Note 9)

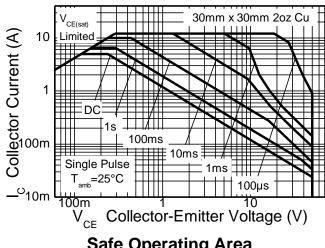
Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	V	3A
Electrostatic Discharge - Machine Model	ESD MM	400	V	С

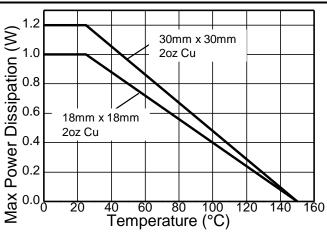
Notes:

^{5.} For a device mounted with the collector lead on 18mm x 18mm 2oz copper that is on a single-sided 1.6mm FR4 PCB; device is measured under still air 5. For a device mounted with the collector lead on 18mm x 18mm 202 copper that is conditions whilst operating in steady-state.
6. Same as note (5), except the device is mounted on 30mm x 30mm 20z copper.
7. Same as note (6), except measured at t < 5 seconds.
8. Thermal resistance from junction to solder-point (at the end of the collector lead).
9. Refer to JEDEC specification JESD22-A114 and JESD22-A115.



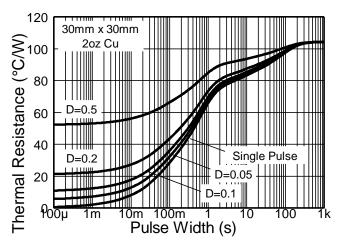
Thermal Characteristics and Derating information

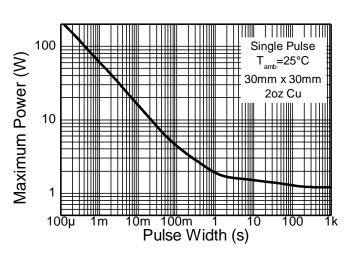




Safe Operating Area

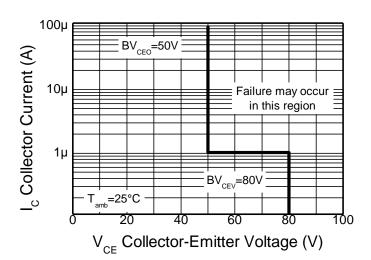
Derating Curve





Transient Thermal Impedance

Pulse Power Dissipation



Safe Operating Area





Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

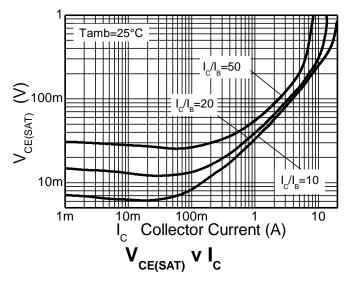
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	BV _{CBO}	80	175	-	V	$I_{C} = 100 \mu A$
Collector-Emitter Breakdown Voltage	BV _{CEV}	80	175	-	V	$I_C = 1\mu A$, $-1V < V_{BE} < +0.3V$
Collector-Emitter Breakdown Voltage (Note 10)	BV _{CEO}	50	75	-	V	$I_C = 10mA$
Emitter-Base Breakdown Voltage	BV _{EBO}	7	8.3	-	V	$I_E = 100\mu A$
Collector – Emitter Cut-Off Current	I _{CEV}	-	<1	20	nA	V _{CE} = 60V, V _{BE} = -1V
Collector - Base Cut-Off Current	I _{CBO}	-	<1	20	nA	V _{CB} = 60V
Emitter Cut-off Current	I _{EBO}	-	<1	10	nA	V _{EB} = 6V
Static Forward Current Transfer Ratio (Note 10)	h _{FE}	190 200 200 80	300 350 340 125	- 560 - -	-	$I_{C} = 10mA$, $V_{CE} = 2V$ $I_{C} = 500mA$, $V_{CE} = 2V$ $I_{C} = 2A$, $V_{CE} = 2V$ $I_{C} = 5A$, $V_{CE} = 2V$
Collector-Emitter Saturation Voltage (Note 10)	V _{CE(sat)}	- - -	13 30 80 135	18 40 110 170	mV	$I_C = 100$ mA, $I_B = 5$ mA $I_C = 1$ A, $I_B = 100$ mA $I_C = 2$ A, $I_B = 40$ mA $I_C = 5$ A, $I_B = 250$ mA
Base-Emitter Saturation Voltage (Note 10)	V _{BE(sat)}	-	800 920	900 1000	mV	$I_C = 2A$, $I_B = 40mA$ $I_C = 5A$, $I_B = 250mA$
Base-Emitter Turn-On Voltage (Note 10)	V _{BE(on)}	-	830	930	mV	$I_{C} = 5A, V_{CE} = 2V$
Transition Frequency	F _T	-	125	-	MHz	I _C = 500mA, V _{CE} = 10V, f=50MHz
Output Capacitance	C _{obo}	-	29	-	pF	V _{CB} = 10V, f=1MHz
Delay Time	t _(d)	-	16	-	ns	
Rise Time	t _(r)	-	27	-	ns	$V_{CC} = 12V, I_C = 2.5A,$
Storage Time	t _(stg)	-	468	-	ns	$I_{B1} = -I_{B1} = 125mA$
Fall Time	t _(f)	-	44	-	ns	

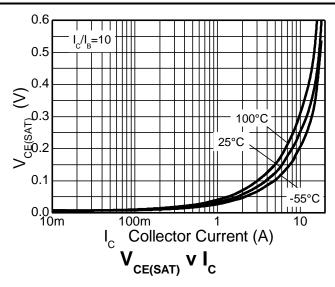
Note:

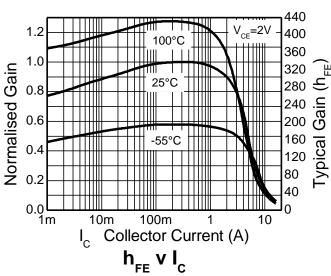
10. Measured under pulsed conditions. Pulse width ≤ 300µs. Duty cycle ≤ 2%

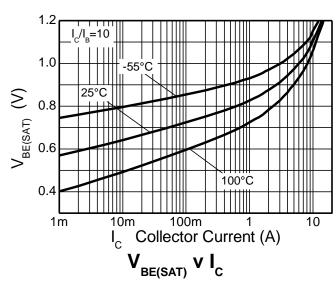


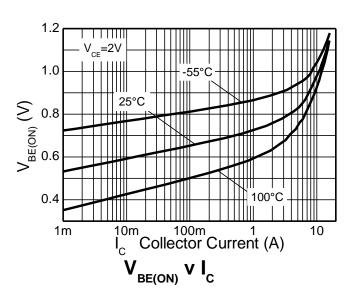
Typical Electrical Characteristics (@TA = +25°C, unless otherwise specified.)







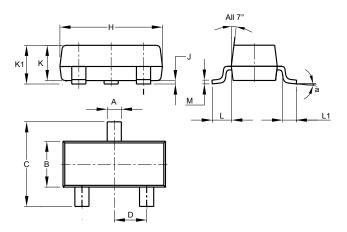






Package Outline Dimensions

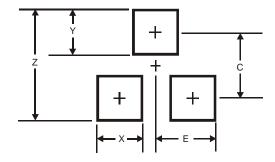
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.



SOT23					
Dim	Min	Max	Тур		
Α	0.37	0.51	0.40		
В	1.20	1.40	1.30		
С	2.30	2.50	2.40		
D	0.89	1.03	0.915		
F	0.45	0.60	0.535		
G	1.78	2.05	1.83		
Н	2.80	3.00	2.90		
J	0.013	0.10	0.05		
K	0.890	1.00	0.975		
K1	K1 0.903 1.10 1.				
L	0.45	0.55			
L1	0.25	0.55	0.40		
M	0.085	0.150	0.110		
а	a 8°				
All	All Dimensions in mm				

Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)			
Z	2.9			
Х	0.8			
Υ	0.9			
С	2.0			
E	1.35			





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